



[10191/1690]

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Volker BECKER et al.

Serial No. : 09/762,985

Filed : May 8, 2001

For : DEVICE AND METHOD FOR ETCHING A SUBSTRATE USING AN INDUCTIVELY COUPLED PLASMA

Art Unit : 1763

Examiner : Luz. L. Alejandro _____
I hereby certify that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to:

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on

Date: 5/28/2003

Signature: Aaron C. Deditch

(33,865)

AMENDMENT

SIR:

In response to the Office Action mailed February 27, 2003 (the three-month response date for which has been extended by one month from May 27, 2003 to June 27, 2003), please reconsider the above-identified application based on the following:

IN THE CLAIMS:

Without prejudice, please amend the claims as follows:

42. (Amended) A method for etching a silicon body substrate using a device having an ICP source for generating a radio-frequency electromagnetic alternating field, a reactor for generating an inductively coupled plasma from reactive particles by the action of the radio-frequency electromagnetic alternating field on a reactive gas, and a first means for generating plasma power pulses to be injected into the inductively coupled plasma by the ICP source, comprising:

matching an impedance of one of an inductive coupled plasma and the ICP source to an ICP coil generator; and

injecting a pulsed radio-frequency power into the inductively coupled plasma as a pulsed plasma power.

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